

AMENDMENTS TO THE CLAIMS:

Claims 1-2 (Canceled).

3. (Currently Amended) A semiconductor apparatus, comprising:
- a substrate having a transistor formed thereon;
 - a plurality of first capacitor electrodes secured to said substrate and;
 - a plurality of second electrodes secured to said substrate and electrically separated from said first electrodes; and
 - an insulating film formed so as to cover said first electrodes and which is between the first electrodes and second electrodes,
- wherein the first and second electrodes have a common bottom level and the plurality of second electrodes each have a top surface which is above a top surface of the first electrodes;
- wherein a distance between a top surface of said substrate and said top surface of the second electrodes is larger than a distance between the top surface of said substrate and the top surface of said an uppermost insulating film formed over the first electrodes.

Claims 4-20. (Canceled).

21. (Currently Amended) A semiconductor apparatus, comprising:

a plurality of first capacitor electrodes secured to a substrate and;

a plurality of discharge electrodes secured to said substrate and electrically separated from said first electrodes and extending above a primary level of an uppermost insulating layer formed above said first capacitor electrodes.

22. (Previously Presented) A semiconductor apparatus, comprising:

a plurality of first capacitor electrodes secured to a substrate and;

a plurality of discharge electrodes secured to said substrate and electrically separated from said first electrodes and extending above a primary level of an uppermost insulating layer formed above said first capacitor electrodes, and further wherein the discharge electrodes have insulation ~~[[on]]~~ over a top surface thereof that is at a level higher than the primary level of the uppermost insulating layer formed above the first capacitor electrodes.